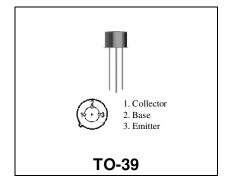


**SD1127** 

# RF & MICROWAVE TRANSISTORS VHF FM MOBILE APPLICATIONS

#### Features

- 175 MHz
- 12.5 VOLTS
- P<sub>OUT</sub> = 4.0 W MINIMUM
- $G_P = 12.0 \text{ dB}$
- GROUNDED EMITTER



#### **DESCRIPTION:**

The SD1127 is a epitaxial silicon NPN transistor designed primarily for VHF mobile communications. The chip of this transistor is mounted on a beryllia pill to isolate the collector lead and ground the emitter lead for high gain performance

## ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	36	V
V <sub>CEO</sub>	Collector-Emitter Voltage	18	V
V <sub>CES</sub>	Collector-Emitter Voltage	36	V
<b>V</b> EBO	Emitter – Base Voltage	4.0	V
<b>I</b> c	Collector Current	.64	Α
Ptot	Total Power Dissipation	8.0	W
T <sub>STG</sub>	Storage Temperature	-65 + 200	°C
TJ	Junction Temperature	+200	°C

### Thermal Data

$R_{TH(J-C)}$	Junction-case Thermal Resistance	21.9	°C/W
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# **SD1127**

# ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

### STATIC

Symbol		Test Conditions		Value		
			Min.	Typ.	Max.	Unit
BV <sub>CES</sub>	$I_C = 5 \text{ mA}$	V <sub>BE</sub> = 0	36			V
BV <sub>CEO</sub>	I <sub>C</sub> = 10 mA	I <sub>B</sub> = 0	18			V
BV <sub>EBO</sub>	I <sub>E</sub> = 1 mA	I <sub>C</sub> = 0	4.0			V
I <sub>CBO</sub>	V <sub>CB</sub> = 15.0 V	I <sub>E</sub> = 0			.25	mA
H <sub>FE</sub>	$V_{CE} = 5.0 \text{ V}$	$I_C = 50 \text{ mA}$	10		100	

### **DYNAMIC**

Symbol		Test Conditions		Value		
			Min.	Typ.	Max.	Unit
P <sub>OUT</sub>	f =175 MHz	$V_{CE} = 12.5 \text{ V}$	4.0			W
G <sub>PE</sub>	f =175 MHz	V <sub>CE</sub> =12.5 V	12.0			dB
Cob	f =1 MHz	V <sub>CE</sub> =15.0 V			20.0	pf

### **IMPEDANCE DATA**

FREQ	$\mathbf{Z}_{IN}(\Omega)$	$\mathbf{Z}_{CL}(\Omega)$
136 MHz	3.0 – j3.8	12.8 – j11
155 MHz	4.0 – j2.0	11 – j14.8
175 MHz	4.3 – j5.8	13 – j20

 $P_{IN} = 0.2W$   $V_{CC} = 12.6V$ 



# **SD1127**

### PACKAGE MECHANICAL DATA

